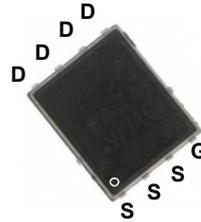
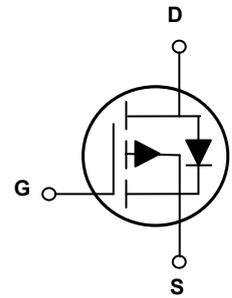


## Main Product Characteristics

$BV_{DSS}$	-30V
$R_{DS(ON)}$	3.3m $\Omega$
$I_D$	-100A



PPAK5X6



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The GSFP03101 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	-100	A
Drain Current-Continuous ( $T_C=100^\circ\text{C}$ )		-63.2	
Drain Current-Pulsed <sup>1</sup>	$I_{DM}$	-400	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	320	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	80	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	138	W
Power Dissipation-De-rate above $25^\circ\text{C}$		1.11	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$

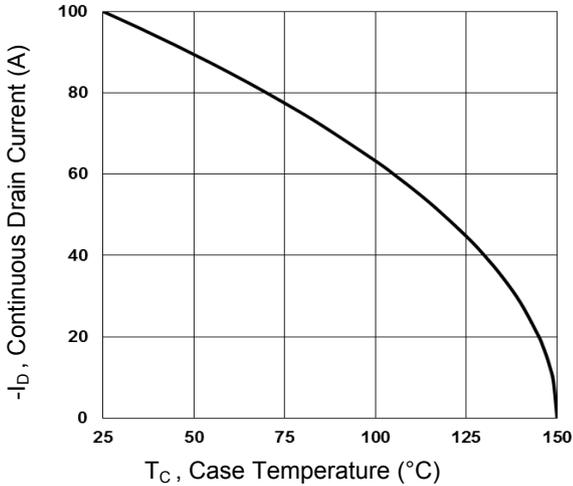
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On/Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	-	-	-1	$\mu A$
		$V_{DS}=-24V, V_{GS}=0V, T_J=125^{\circ}\text{C}$	-	-	-10	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-30A$	-	2.6	3.3	m $\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	-	3.8	5	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.2	V
Forward Transconductance	$g_{fs}$	$V_{DS}=-10V, I_D=-3A$	-	20	-	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>3,4</sup>	$Q_g$	$V_{DS}=-24V, I_D=-10A, V_{GS}=-10V$	-	146	210	nC
Gate-Source Charge <sup>3,4</sup>	$Q_{gs}$		-	22	44	
Gate-Drain Charge <sup>3,4</sup>	$Q_{gd}$		-	32	64	
Turn-On Delay Time <sup>3,4</sup>	$t_{d(on)}$	$V_{DD}=-15V, R_G=5\Omega, V_{GS}=-10V, I_D=-10A$	-	17	34	nS
Rise Time <sup>3,4</sup>	$t_r$		-	61	120	
Turn-Off Delay Time <sup>3,4</sup>	$t_{d(off)}$		-	200	400	
Fall Time <sup>3,4</sup>	$t_f$		-	113	220	
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V, F=1\text{MHz}$	-	7930	12000	pF
Output Capacitance	$C_{oss}$		-	983	1300	
Reverse Transfer Capacitance	$C_{rss}$		-	505	750	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_S$	$V_G=V_D=0V,$ Force Current	-	-	-100	A
Pulsed Source Current	$I_{SM}$		-	-	-200	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1A, T_J=25^{\circ}\text{C}$	-	-	-1	V
Reverse Recovery Time	$T_{rr}$	$V_{GS}=0V, I_S=-20A, di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	-	52	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	53	-	nC

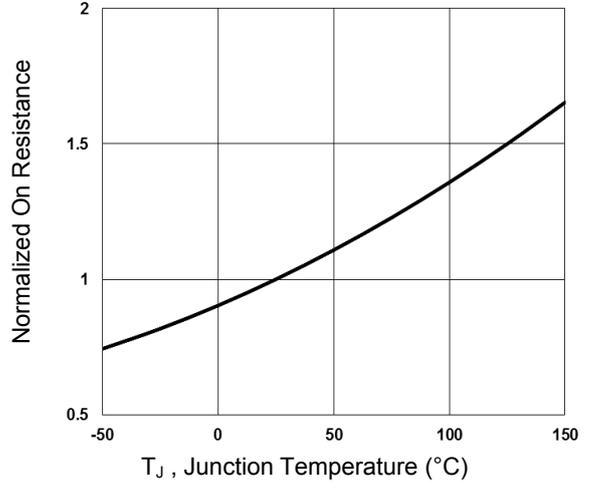
Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=80A, R_G=25\Omega,$  starting  $T_J=25^{\circ}\text{C}$ .
3. Pulse test: pulse width  $\leq 300\mu s,$  duty cycle  $\leq 2\%$ .
4. Essentially independent of operation temperature.

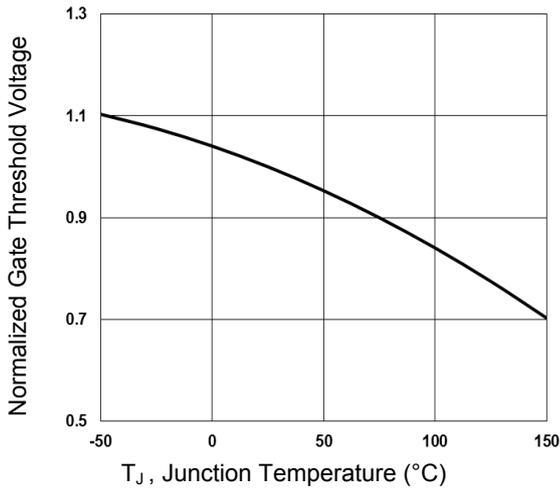
**Typical Electrical and Thermal Characteristic Curves**



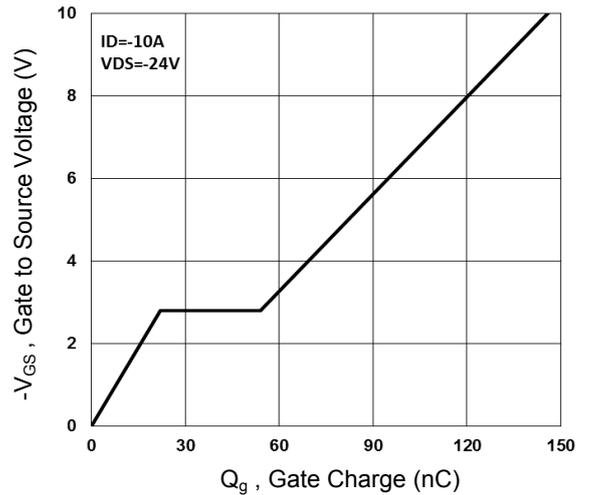
**Figure 1. Continuous Drain Current vs.  $T_C$**



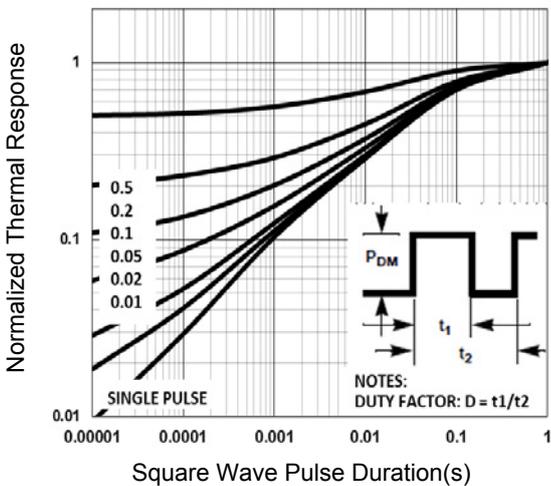
**Figure 2. Normalized  $R_{DS(ON)}$  vs.  $T_J$**



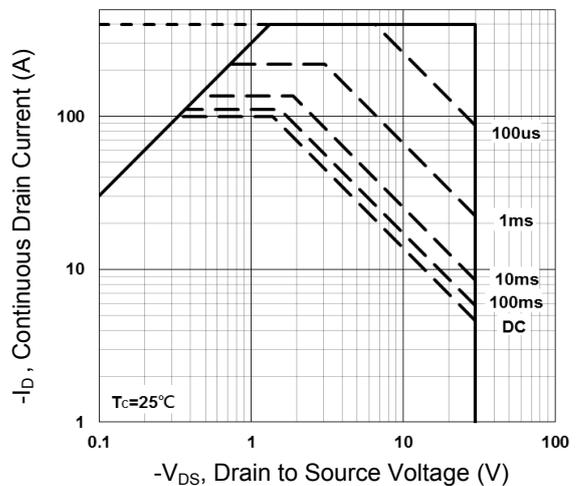
**Figure 3. Normalized  $V_{th}$  vs.  $T_J$**



**Figure 4. Gate Charge Waveform**

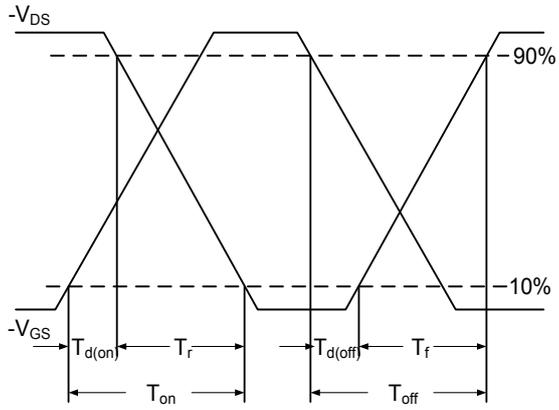


**Figure 5. Normalized Transient Impedance**

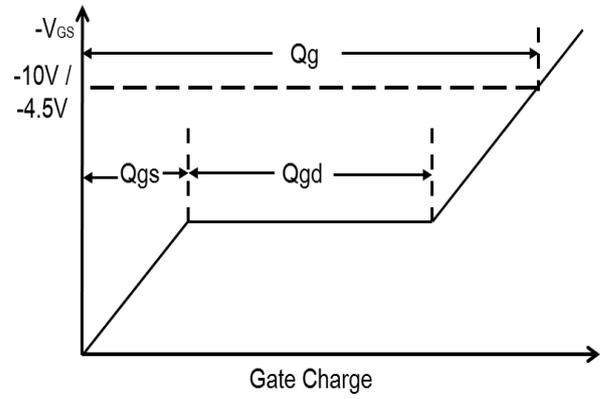


**Figure 6. Maximum Safe Operation Area**

**Typical Electrical and Thermal Characteristic Curves**

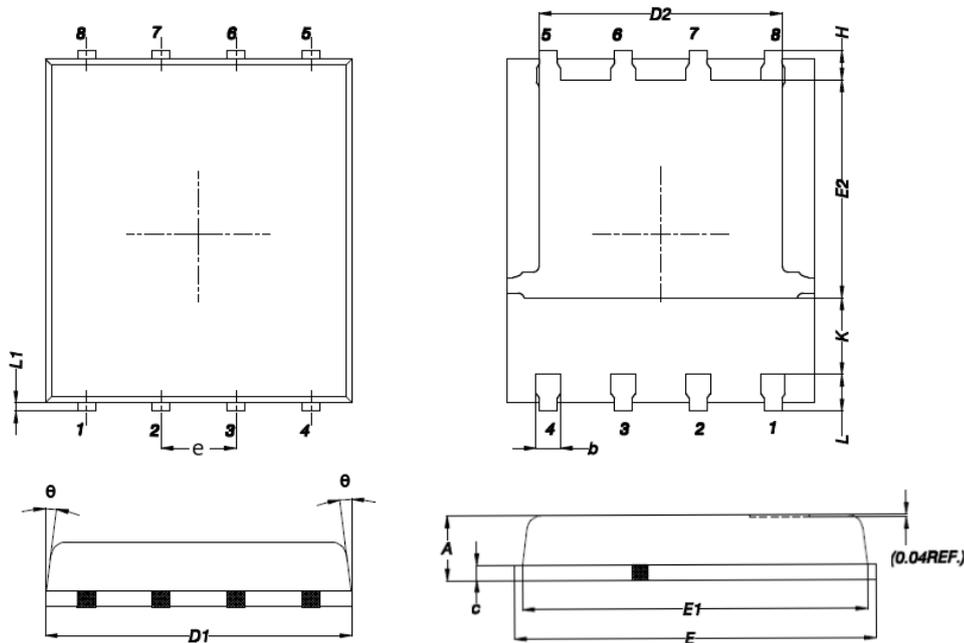


**Figure 7. Switching Time Waveform**



**Figure 8. Gate Charge Waveform**

**Package Outline Dimensions (PPAK5x6)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.300	0.020	0.012
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	-	1.100	-	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°

**Order Information**

MPN	Package	Marking Code	Carrier	Quantity	HSF Status
GSFP03101	PPAK5x6	DC3901X	Tape & Reel	3000/Reel	RoHS Compliant